

Contents of Applied Physics A 56

This listing presents the papers in alphabetical order of the first author, subdivided into the sections "Solids and Materials: Physical and Chemical Properties" and "Surfaces and Multilayers: Growth, Modification, and Integration". The Author Index that follows covers *Applied Physics A* and *B*, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second and third columns contain the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The PACS numbers given in the fourth column may be used in conjunction with the PACS listing on the left to infer the topic of a paper.

Solids and Materials

Antoncić E.

The influence of the solubility limit on diffusion of As implants in silicon.

Appl. Phys. A 56/4, 291-298 (1993) PACS: 61.70T 66.30 64.75

Arafah D.-E., Al-Ramadin Y.

Radiation-enhanced diffusion in ion-implanted glass.

Appl. Phys. A 56/6, 555-559 (1993) PACS: 61.80 66.30 42.70

Auret F.D., Goodman S.A., Myburg G., Meyer W.E.

Electrical characterization of defects introduced in n-GaAs by alpha and beta irradiation from radionuclides.

Appl. Phys. A 56/6, 547-553 (1993) PACS: 81.40R 61.80

Byrne H.J., Maser W.K., Rühle W.W., Mittelbach A., Roth S.

Nonlinear luminescence phenomena in fullerene crystallites.

Appl. Phys. A 56/3, 235-239 (1993) PACS: 33.50D 42.65 42.70

Castro J., Rivas J.

On the magnetic after-effect (MAE) in magnetite at high temperatures.

Appl. Phys. A 56/4, 323-327 (1993) PACS: 61.70 75.50

Cruz H., Muñoz A.

Dynamics of resonant and non-resonant tunneling in asymmetric coupled quantum wells.

Appl. Phys. A 56/1, 40-42 (1993) PACS: 73.40G 72.80 73.20

Dietz P., Hansma P., Fostiropoulos K., Krätschmer W.

Atomic force microscopy of C_{60}/C_{70} single-crystal fullerenes under ethanol.

Appl. Phys. A 56/3, 207-210 (1993) PACS: 61.16D 68.35

Fischer J.E., Werwa E., Heiney P.A.

Pseudo-epitaxial C_{60} films prepared by a hot-wall method.

Appl. Phys. A 56/3, 193-196 (1993) PACS: 68.55 81.15

Gelfand M.P., Lu J.P.

Orientational correlations and order in A_3C_{60} . Consequences for density of states and conductivity.

Appl. Phys. A 56/3, 215-217 (1993) PACS: 71.25M 71.25 71.20 36.40

Gensterblum G., Yu L.-M., Pireaux J.-J., Thiry P.A., Caudano R., Themlin J.-M., Bouzidi S., Coletti F., Debever J.-M.

C_{60} growth on Si(100), GaSe(0001) and GeS(001). Influence of the substrate on the film crystallinity.

Appl. Phys. A 56/3, 175-183 (1993) PACS: 68.55 73.60 79.20

Haegel N.M., Latasa C.A., White A.M.

Transient response of infrared photoconductors: The roles of contacts and space charge.

Appl. Phys. A 56/1, 15-21 (1993) PACS: 72.40 72.20

Haluska M., Kuzmany H., Vybormov M., Rogl P., Fejdi P.

A double-temperature-gradient technique for the growth of single-crystal fullerenes from the vapor phase.

Appl. Phys. A 56/3, 161-167 (1993) PACS: 61.50C 81.10 61.50

Humlicek J., Garriga M.

Temperature dependence of the refractive index of crystalline germanium-silicon alloys.

Appl. Phys. A 56/3, 259-261 (1993) PACS: 78.20C 78.40

Jonscher A.K.

Energy criterion in the interpretation of dielectric relaxation.

Appl. Phys. A 56/5, 405-408 (1993) PACS: 66.00 72.20 77.00

Kaiser J.H.

Microwave evaluation of the conductive filler particles of carbon black-rubber composites.

Appl. Phys. A 56/4, 299-303 (1993) PACS: 72.20 73.40 82.70

Kamarás K., Breitschwerdt A., Pekker S., Fodor-Csorba K., Faigl G., Tegze M.

Shift of the optical absorption edge in C_{60} clathrate single crystals.

Appl. Phys. A 56/3, 231-233 (1993) PACS: 78.20D

Krakow W., Rivera N.M., Roy R.A., Ruoff R.S., Cuomo J.J.

The growth of crystalline vapor deposited carbon-60 thin films.

Appl. Phys. A 56/3, 185-192 (1993) PACS: 61.10 68.55

Kremer R.K., Rabenau T., Maser W.K., Kaiser M., Simon A.,

Haluska M., Kuzmany H.

High-temperature conductivity study on single-crystal C_{60} .

Appl. Phys. A 56/3, 211-214 (1993) PACS: 72.20

Kukhtarev N., Dovgaleiko G., Shultz J., Salamo G., Sharp E.J.,

Wechsler B.A., Klein M.B.

Manifestation of circular photogalvanic current by dynamic holography in $BaTiO_3$.

Appl. Phys. A 56/4, 303-305 (1993) PACS: 42.40 42.65 42.70

Lang H.P., Thommen-Geiser V., Bolm C., Felder M., Frommer J.,

Wiesendanger R., Werner H., Schlögl R., Zahab A., Bernier P., Gerth G.,

Anselmetti D., Güntherodt H.-J.

Determination of C_{60}/C_{70} ratios in fullerene mixtures and film characterization by scanning tunneling microscopy.

Appl. Phys. A 56/3, 197-205 (1993) PACS: 36.40 61.16 68.20

Lim B.S., Vaysleyb A.V., Nowick A.S.

Nature of the constant-loss dielectric response of various crystals and glasses.

Appl. Phys. A 56/1, 8-14 (1993) PACS: 66.90 77.40

Malovichko G.I., Grachev V.G., Kokanyan E.P., Schirmer O.F.,

Betzler K., Gather B., Jermann F., Klauer S., Wöhlecke M.

Characterization of stoichiometric $LiNbO_3$ grown from melts containing K_2O .

Appl. Phys. A 56/2, 103-108 (1993) PACS: 77.80 76.30 61.50 78.20

Matus M., Kuzmany H.

Raman spectra of single-crystal C_{60} .

Appl. Phys. A 56/3, 241-248 (1993) PACS: 78.30 61.50 61.80

Meingast C., Gugenberger F., Haluska M., Kuzmany H., Roth G.

Phase transition at 240 K in C_{70} single crystal.

Appl. Phys. A 56/3, 227-229 (1993) PACS: 31.70K 64.70 65.70

Müllenborn M., Jarvis Jr. R.F., Yacobi B.G., Kaner R.B., Coleman C.C.,

Haegel N.M.

Characterization of solution-synthesized CdTe and HgTe.

Appl. Phys. A 56/4, 317-321 (1993) PACS: 78.55E 81.10 61.16

Ori O., D'Mello M.

Analysis of the structure of the C_{78} fullerene: A topological approach.

Appl. Phys. A 56/1, 35-39 (1993) PACS: 61.50E

Ossipyan Yu.A., Bobrov V.S., Grushko Yu.S., Dilanyan R.A.,

Zharikov O.V., Lebyodkin M.A., Shekhtman V.Sh.

On the mechanical properties of C_{60} fullerite crystals.

Appl. Phys. A 56/5, 413-416 (1993) PACS: 61.46

Palm H., Arbes M., Schulz M.

Nanometer-microscopy of the electron transmission through an ultrathin (3 ± 2 nm) Au film and of the Au-Si Schottky barrier height.

Appl. Phys. A 56/1, 1-7 (1993) PACS: 61.16D 68.35 73.30 73.40

Petrocelli G., Martellucci S., Francini R.

Wavelength dependence of second-harmonic generation at the copper surface.

Appl. Phys. A 56/3, 263-266 (1993) PACS: 42.65K 78.65

Philippart V., Dumont M., Nunzi J.M., Charra F.

Femtosecond Kerr ellipsometry in polydiacetylene solutions: Two-photon effects.

Appl. Phys. A 56/1, 29-34 (1993) PACS: 42.65 78.65

Rao D.V., Cesaro R., Gigante G.E.

K X-ray fluorescence cross-sections for some light elements excited by keV photons.

Appl. Phys. A 56/5, 401-403 (1993) PACS: 78.55H 78.70

Roth G., Adelman P.

Preparation and crystal structure of $C_{60}S_{16}$.

Appl. Phys. A 56/3, 169-174 (1993) PACS: 61.50 61.10

Schlarb U., Klauer S., Wesselmann M., Betzler K., Wöhlecke M.

Determination of the Li/Nb ratio in lithium niobate by means of birefringence and Raman measurements.

Appl. Phys. A 56/4, 311-315 (1993) PACS: 78.20F 78.30 81.70

Shamonin M.

Soliton-shaped nonlinear waves of space charge in photorefractive materials.

Appl. Phys. A 56/5, 467-468 (1993) PACS: 42.50 42.65

Tan T.Y., You H.-M., Gösele U.M.

Thermal equilibrium concentrations and effects of negatively charged Ga vacancies in n-type GaAs.

Appl. Phys. A 56/3, 249-258 (1993) PACS: 61.70B 61.70 66.30

Tea N.H., Yu R.-C., Salamon M.B., Lorents D.C., Malhotra R.,

Ruoff R.S.

Thermal conductivity of C_{60} and C_{70} crystals.

Appl. Phys. A 56/3, 219-225 (1993) PACS: 66.70 64.70 61.50

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Plasma and surface modeling of the deposition of hydrogenated carbon films from low-pressure methane plasmas.
Appl. Phys. A 56/6, 527-546 (1993) PACS: 52.25D 79.20 82.65
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Modeling of gas-phase processes in laser-induced chemical vapor deposition from $\text{Cr}(\text{CO})_6$ with an excimer laser.
Appl. Phys. A 56/2, 138-146 (1993) PACS: 81.15 68.55 82.20
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Appl. Phys. A 56/4, 375-380 (1993) PACS: 85.30
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Coupled relaxation oscillators for frequency multiplication.
Appl. Phys. A 56/5, 437-442 (1993) PACS: 82.25J
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Pulsed ultraviolet laser ablation.
Appl. Phys. A 56/1, 51-63 (1993) PACS: 42.10 81.60
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The concept of quasi-discrete levels for ion-implanted waveguides.
Appl. Phys. A 56/5, 449-451 (1993) PACS: 42.80L
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Phase transition study of H:LiNbO_3 waveguides by Raman spectroscopy.
Appl. Phys. A 56/1, 81-86 (1993) PACS: 64.70 78.30 78.65
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Early stages of laser mixing process in Sb/Ge multilayer thin films.
Appl. Phys. A 56/2, 132-137 (1993) PACS: 64.75 78.90 81.40
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Electrical properties of $\text{p}^+/\text{n}^+ \text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ tunnel diodes grown by liquid phase epitaxy.
Appl. Phys. A 56/2, 153-155 (1993) PACS: 72.20 85.30 81.10
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Use of Langmuir probes for monitoring of precursor concentrations during plasma activated chemical vapor deposition of hard coatings.
Appl. Phys. A 56/5, 443-444 (1993) PACS: 81.15G 52.70 52.90
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Ablation of polyimide (KaptonTM) films by pulsed (ns) ultraviolet and infrared ($9.17\mu\text{m}$) lasers. A comparative study.
Appl. Phys. A 56/5, 417-423 (1993) PACS: 42.60 82.65 73.40
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Appl. Phys. A 56/1, 91-94 (1993) PACS: 68.55 61.14 82.65 61.50
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Appl. Phys. A 56/2, 109-112 (1993) PACS: 78.65F 71.35 73.20
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Monte-Carlo study of reactive ion-beam assisted film growth.
Appl. Phys. A 56/6, 561-565 (1993) PACS: 68.55 79.20
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A comparison of confining potentials in the quantum wire problem.
Appl. Phys. A 56/2, 127-131 (1993) PACS: 73.20D 73.50 72.10